

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-30V	8mΩ@-10V	-15A
	10.5mΩ@-4.5V	

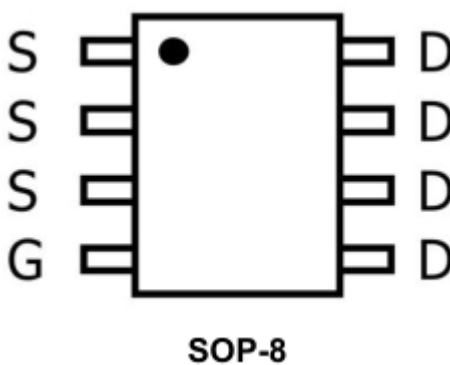
Feature

- $V_{DS} = -30V, I_D = -15A$,
 $R_{DS(ON)} < 12m\Omega @ V_{GS} = -10V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package.

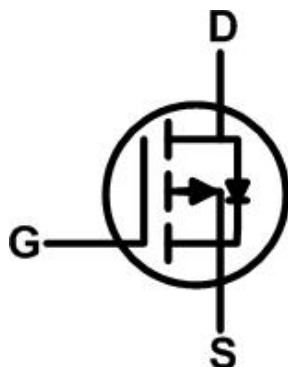
Application

- Power management
- Load switch

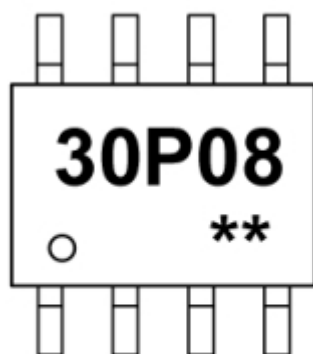
Package



Circuit diagram



Marking



30P08 =Device Code
** =Week Code

Absolute maximum ratings

($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-15	A
Drain Current-Pulsed ¹	I_{DM}	-60	A
Maximum Power Dissipation	P_D	3.1	W
Thermal Resistance,Junction-to-Ambient ²	$R_{\theta JA}$	40	$^{\circ}\text{C}/\text{W}$
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^{\circ}\text{C}$

Electrical characteristics

($T_A=25^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$BV_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30V, V_{GS} = 0V$			-1	μA
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	μA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1	-1.6	-2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -15A$		8	12	m Ω
		$V_{GS} = -4.5V, I_D = -10A$		10.5	15	
Forward Transconductance	g_{FS}	$V_{DS} = -10V, I_D = -15A$	30			S
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = -15V, V_{GS} = 0V, f = 1MHz$		2900		pF
Output Capacitance	C_{oss}			410		
Reverse Transfer Capacitance	C_{rss}			280		
Switching Characteristics						
Turn-on Delay Time	$T_{d(on)}$	$V_{DD} = -15V, I_D = -10A, V_{GS} = -10V, R_{GEN} = 3\Omega$		15		nS
Turn-on Rise Time	T_r			11		
Turn-off Delay Time	$T_{d(off)}$			44		
Turn-off Fall Time	T_f			21		
Total Gate Charge	Q_g	$V_{DS} = -15V, I_D = -10A, V_{GS} = -10V$		48		nC
Gate-Source Charge	Q_{gs}			12		
Gate-Drain Charge	Q_{gd}			14		
Drain-Source Diode Characteristics						
Diode Forward Voltage ³	V_{SD}	$V_{GS} = 0V, I_S = -2A$			-1.2	V

Note:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Characteristics

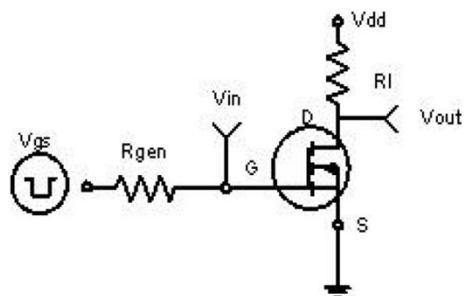


Figure 1 Switching Test Circuit

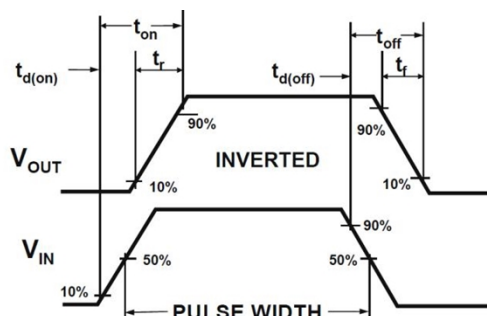


Figure 2 Switching Waveforms

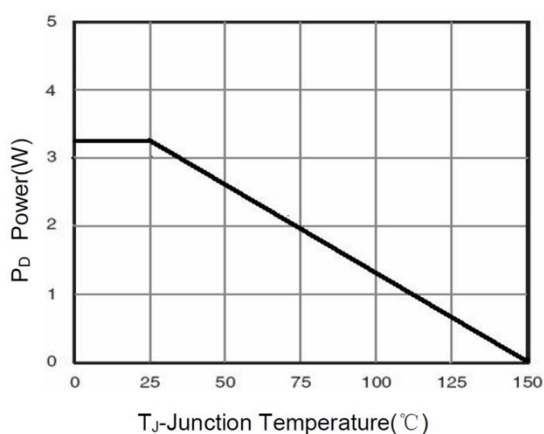


Figure 3 Power Dissipation

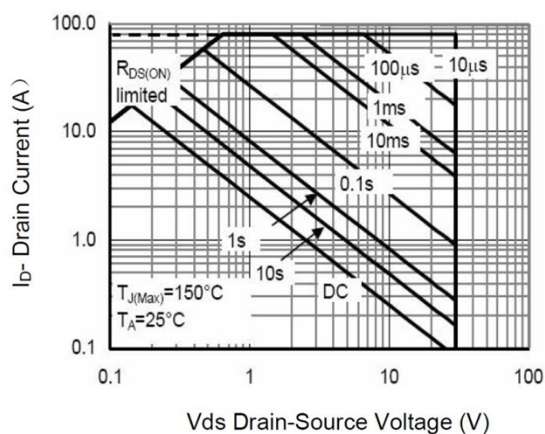


Figure 4 Safe Operation Area

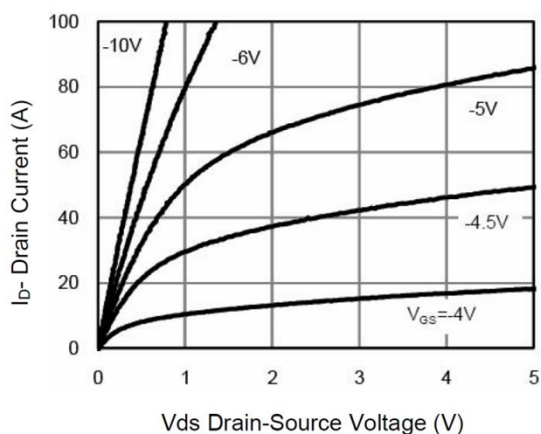


Figure 5 Output Characteristics

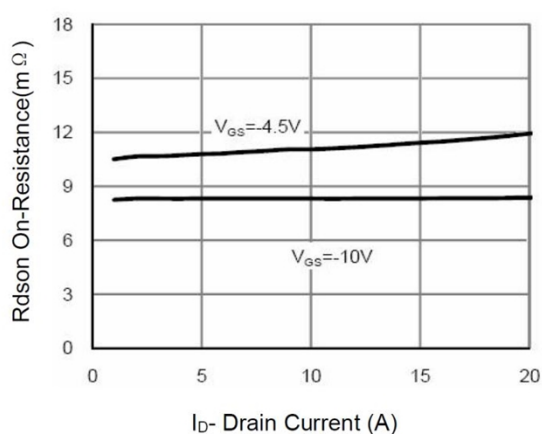


Figure 6 Drain-Source On-Resistance

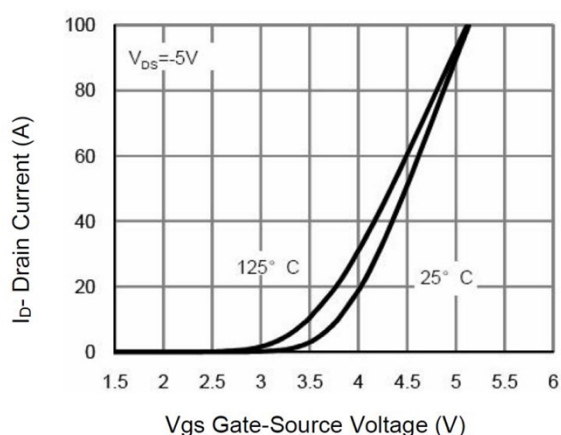


Figure 7 Transfer Characteristics

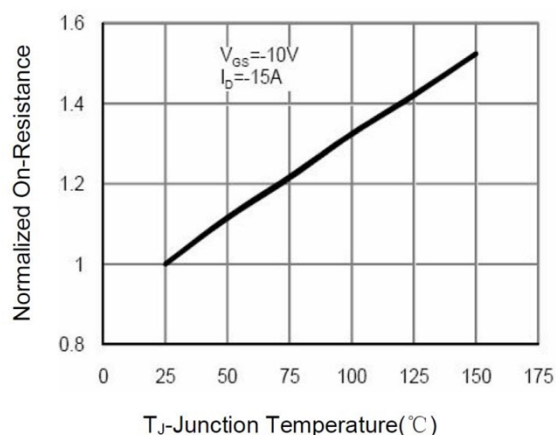


Figure 8 Drain-Source On-Resistance

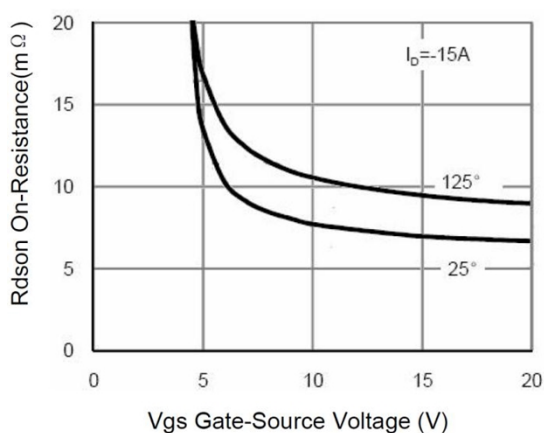


Figure 9 Rdson vs Vgs

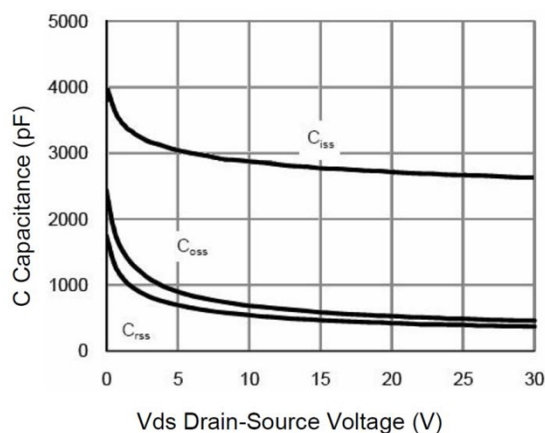


Figure 10 Capacitance vs Vds

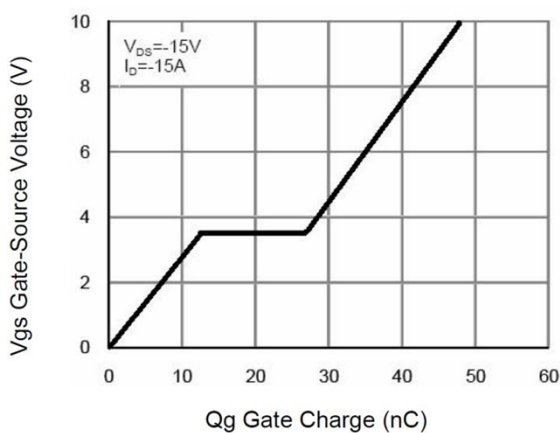


Figure 11 Gate Charge

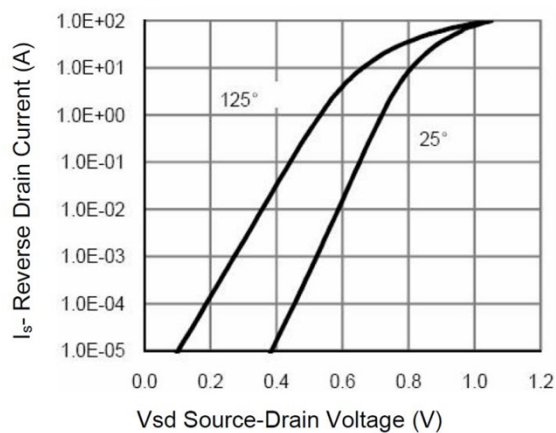


Figure 12 Source- Drain Diode Forward

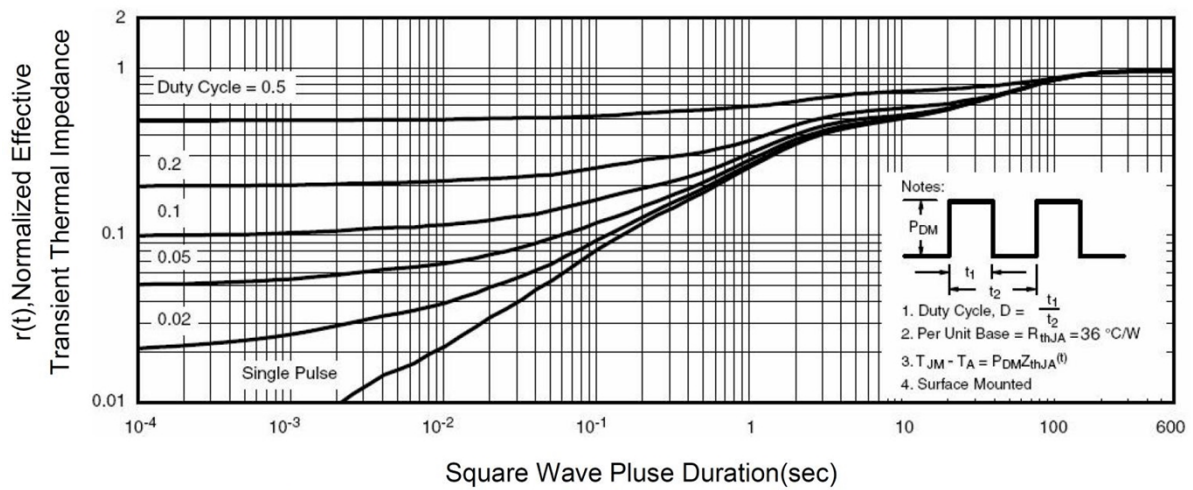
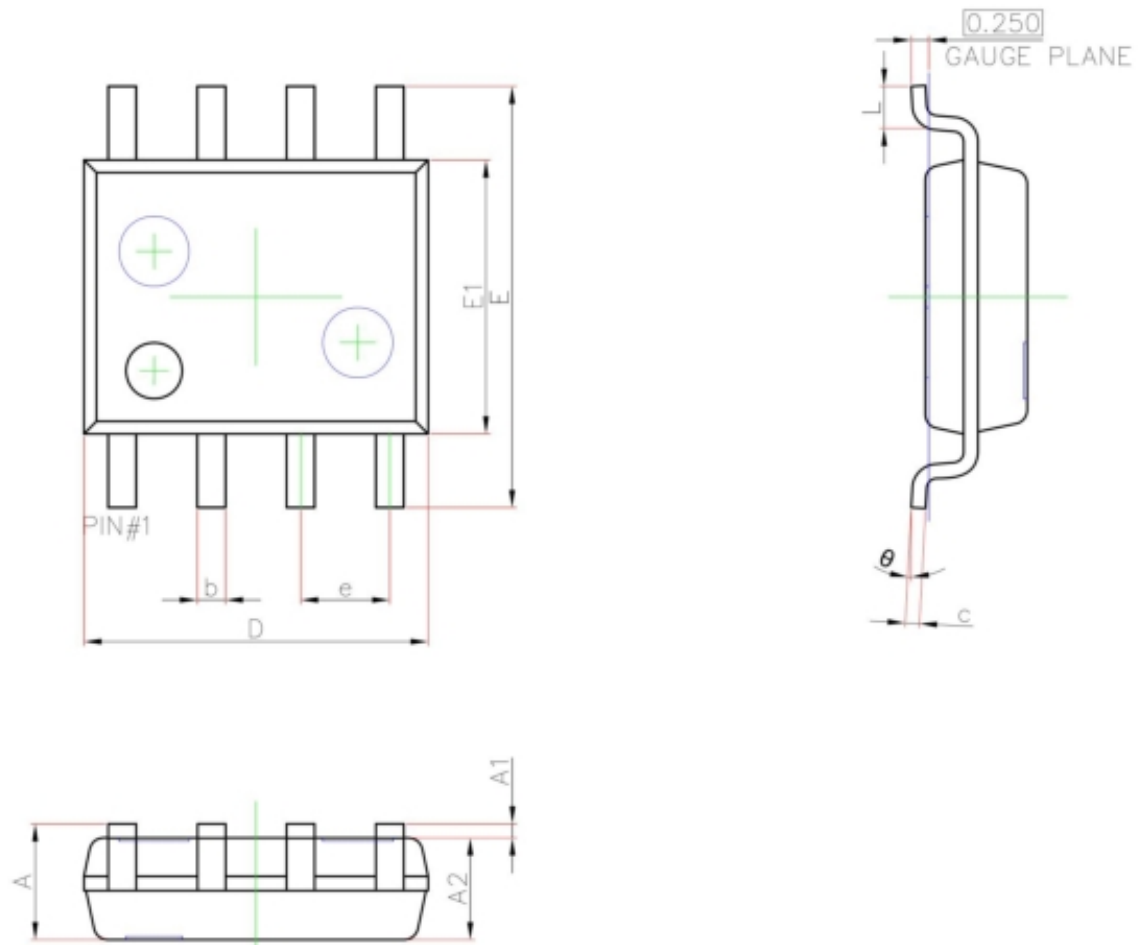


Figure 13 Normalized Maximum Transient Thermal Impedance

SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.450	1.750	0.057	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.700	5.100	0.185	0.201
E	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°